(02S1239)

As a below named inventor, I declare that my residence, mailing address and citizenship are as stated below above my name; I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

the specification of which (check applicable b	oox(es))	
 [] is attached hereto. [X] was filed on September 30, 2003 or PCT International Application No. [] and was amended on 	as United States Application No.	10/673,262

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR 1.56

I hereby claim foreign priority benefits under 35 U.S.C. 119(a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 35 U.S.C. 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed:

None

I hereby claim the benefit under 35 U.S.C. 119(e) of any United States provisional applications listed below.

I hereby claim the benefit under 35 U.S.C. 120 of any United States application(s) or 35 U.S.C. 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application or PCT International application in the manner provided by the first paragraph of 35 U.S.C. 112, I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR 1.56, which became available between the filing date of the prior application and the national or PCT international filing date of this application.

I hereby appoint as my attorneys, with full power of substitution and revocation, to prosecute this application and transact all business in the Patent and Trademark Office connected therewith: the registrants of Oblon, Spivak, McClelland, Maier & Neustadt, P.C., Fourth Floor, 1755 Jefferson Davis Highway, Arlington, Virginia 22202, Customer No. 22850, or any one of them. Send correspondence to Oblon, Spivak, McClelland, Maier & Neustadt, P.C., Fourth Floor, 1755 Jefferson Davis Highway, Arlington, Virginia 22202.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

€.		
DECLARATION FOR PAT		2S1239)
	n, Toshiba Corporation, 1-1, Shibaura 1	l-chome,
Minato ku, Tokyo 105-8001, Japan Residence Address: Yokohama shi, Japan Citizenship: Japan		
Kertono Imai	FEB 4. 2004	
Keitaro Imai	Date:	
·	,	
[2nd Inventor] Mailing Address: c/o Intellectual Property Division Minato·ku, Tokyo 105·8001, Japan Residence Address: Tokyo, Japan Citizenship: Japan	n, Toshiba Corporation, 1-1, Shibaura 1	l-chome,
Kojo Jamle	FEB 4. 2004	
Koji Yamakawa	Date:	
[3rd Inventor] Mailing Address: c/o Intellectual Property Division Minato-ku, Tokyo 105-8001, Japan Residence Address: Yokohama-shi, Japan Citizenship: Japan	n, Toshiba Corporation, 1-1, Shibaura 1	l-chome,
Work Johnne	FEB 4. 2004	
Hiroshi Itokawa	Date:	•
	•	
[4th Inventor] Mailing Address: c/o Intellectual Property Division Minato-ku, Tokyo 105-8001, Japan Residence Address: Yokohama-shi, Japan Citizenship: Japan		l-chome,
121106:	FEB 4, 2004	

DECLARATION FOR PATE	NT APPI	LICATION		(02S1239
[5th Inventor] TRADER				
Mailing Address: c/o Intellectual Property Division,	Toshiba	Corporation,	1-1, Shibaur	a 1-chome
Minato-ku, Tokyo 105-8001, Japan				
Residence Address: Yokohama shi, Japan				
Citizenship: Japan				
Dome trisum		FFR -	- 4. 2004	
Doamu Fisumi			4, 2004	
Osamu Arisumi	Date:			
		•		
[6th Inventor]	m 1 '1		1 1 (1)	1 1
Mailing Address: c/o Intellectual Property Division,	Toshiba	Corporation,	1.1, Shibaur	a 1-cnome
Minato ku, Tokyo 105-8001, Japan Residence Address: Tokyo, Japan				
Citizenship: Japan				
		חחח	4 0004	
Keisuke Nakazawa Keisuke Nakazawa		FEB. –	4. 2004	
Keisuke Nakazawa	Date:			
[7th Inventor]				
Mailing Address: Shurosu-Senzoku B, 6-30-9, Hatanodai,	, Shinaga	iwa-ku, Tokyo	, Japan	
Residence Address: Tokyo, Japan				

Citizenship: Korea

Bum-ki Moon	Date:

(02S1239)

below named inventor, I declare that my residence, mailing address and citizenship are as stated below above my name; I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

the specification of which (check applicable box(es))
 [] is attached hereto. [X] was filed on September 30, 2003 as United States Application No. 10/673,262 or PCT International Application No. [] and was amended on
I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above. I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR
1.56.
I hereby claim foreign priority benefits under 35 U.S.C. 119(a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 35 U.S.C. 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below
any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed:
Hillig date before that of the application on withou priority is claimed.

I hereby claim the benefit under 35 U.S.C. 119(e) of any United States provisional applications listed below.

I hereby claim the benefit under 35 U.S.C. 120 of any United States application(s) or 35 U.S.C. 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application or PCT International application in the manner provided by the first paragraph of 35 U.S.C. 112, I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR 1.56, which became available between the filing date of the prior application and the national or PCT international filing date of this application.

I hereby appoint as my attorneys, with full power of substitution and revocation, to prosecute this application and transact all business in the Patent and Trademark Office connected therewith: the registrants of Oblon, Spivak, McClelland, Maier & Neustadt, P.C., Fourth Floor, 1755 Jefferson Davis Highway, Arlington, Virginia 22202, Customer No. 22850, or any one of them. Send correspondence to Oblon, Spivak, McClelland, Maier & Neustadt, P.C., Fourth Floor, 1755 Jefferson Davis Highway, Arlington, Virginia 22202.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

(02S1239)

[1st Inventor] A Mailing Address: c/o Intellectual Property Division, Minato-ku, Tokyo 105-8001, Japan Residence Address: Yokohama-shi, Japan Citizenship: Japan	Toshiba	Corporation,	1-1,	Shibaura	1-chome,
Keitaro Imai	Date	:		,	
[2nd Inventor] Mailing Address: c/o Intellectual Property Division, Minato-ku, Tokyo 105-8001, Japan Residence Address: Tokyo, Japan	Toshiba	Corporation,	1-1,	Shibaura	1-chome,
Citizenship: Japan					
[3rd Inventor] Mailing Address: c/o Intellectual Property Division, Minato-ku, Tokyo 105-8001, Japan	Date:	-	1-1,	Shibaura	1 chome,
Residence Address: Yokohama shi, Japan Citizenship: Japan	 	·			
Hiroshi Itokawa	Date:				
[4th Inventor] Mailing Address: c/o Intellectual Property Division, Minato-ku, Tokyo 105-8001, Japan Residence Address: Yokohama-shi, Japan Citizenship: Japan	Toshiba	Corporation,	1-1,	Shibaura	1-chome
Katsuaki Natori	Date	:			

(02S1239)

[5th Inventor] BANE Mailing Address: c/o Intellectual Property Division, Toshiba Corporation, 1-1, Shibaura 1-chome, Minato-ku, Tokyo 105-8001, Japan Residence Address: Yokohama-shi, Japan Citizenship: Japan Date: Osamu Arisumi [6th Inventor] Mailing Address: c/o Intellectual Property Division, Toshiba Corporation, 1·1, Shibaura 1·chome, Minato ku, Tokyo 105-8001, Japan Residence Address: Tokyo, Japan Citizenship: Japan Date: Keisuke Nakazawa c/o Infineon Technologies North America Corp., 1983 Route. 52, Suite 1, [7th Inventor] Hopewell Junction, New York 12533, U.S.A. Mailing Address: Residence Address: New York Citizenship: Korea Jan. 22nd, 2004

Bum-ki Moon

Date: